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| PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE CITATION (Use several sheets if necessary) | | APPLICANT | |
| | | Masayasu MIYATA | |
| Sheet 1 of 1 | | FILING DATE | GROUP |
| | | August 9, 2006 | 2814 |

| U.S. PATENT DOCUMENTS | | | | | | |
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| Ref. Desig. | Examiner's Initials | Document Number | Date | Name | Class/ Subclass | (If appropriate) Filing Date |
| 1. | | 6,821,566 | 11/23/2004 | Nakamura et al. | | |

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| 4. | | Shin-ichi Saito et. al., Inversion Electron Mobility Affected by Phase Separation in High-Permittivity Gate Dielectrics, Jpn. J. Appl. Phys., Japan, The Japan Society of Applied Physics, December 1, 2003, Part 2, No. 12A, Vol. 42 (2003), L1425-L1428. | | | | |

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